

# 2N1722 JAN, JTX

# 2N1724 JAN, JTX



Processed per MIL-PRF-19500/262

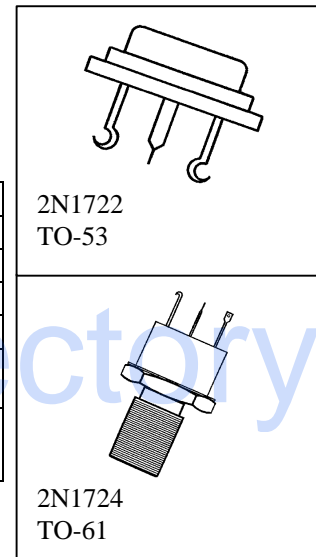
## NPN SILICON HIGH-POWER TRANSISTOR

### MAXIMUM RATINGS

Ratings	Symbol	2N1722 / 2N1724	Units
Collector-Emitter Voltage	$V_{CEO}$	80	Vdc
Collector-Base Voltage	$V_{CBO}$	175	Vdc
Emitter-Base Voltage	$V_{EBO}$	10	Vdc
Collector Current	$I_C$	5.0	Adc
Total Power Dissipation @ $T_A = 25^{\circ}\text{C}^{(1)}$ @ $T_C = 100^{\circ}\text{C}^{(2)}$	$P_T$	3.0	W
		50	W
Temperature Range: Operating	$T_{OP}$	175	$^{\circ}\text{C}$
	Storage Junction	$T_{stg}$	

1) Derate linearly 20 mW/ $^{\circ}\text{C}$  for  $T_A$  between +25 $^{\circ}\text{C}$  and +175 $^{\circ}\text{C}$

2) Derate linearly 666 mW/ $^{\circ}\text{C}$  for  $T_C$  between +100 $^{\circ}\text{C}$  and +175 $^{\circ}\text{C}$



### ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
<b>OFF CHARACTERISTICS</b>				
Collector-Emitter Breakdown Voltage $I_C = 200 \text{ mAdc}$	$V_{(BR)CEO}$	80		Vdc
Emitter-Base Breakdown Voltage $I_E = 10 \text{ mAdc}$	$V_{(BR)EBO}$	10		Vdc
Collector-Emitter Cutoff Current $V_{CE} = 60 \text{ Vdc}$	$I_{CES}$		300	$\mu\text{Adc}$
Collector-Base Cutoff Current $V_{CB} = 175 \text{ Vdc}$	$I_{CBO}$		5.0	mAdc
Emitter-Base Cutoff Current $V_{EB} = 7.0 \text{ Vdc}$	$I_{EBO}$		400	$\mu\text{Adc}$
<b>ON CHARACTERISTICS</b>				
Forward-Current Transfer Ratio $I_C = 2.0 \text{ Adc}, V_{CE} = 15 \text{ Vdc}$ $I_C = 5.0 \text{ Adc}, V_{CE} = 15 \text{ Vdc}$ $I_C = 100 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}$	$h_{FE}$	30 15 30	120	

**2N1722, 2N1724 JAN SERIES**

**ELECTRICAL CHARACTERISTICS (con't)**

Characteristics	Symbol	Min.	Max.	Unit
Collector-Emitter Saturation Voltage $I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mAdc}$	$V_{CE(sat)}$		0.6	Vdc
Base-Emitter Saturation Voltage $I_C = 2.0 \text{ Adc}, I_B = 200 \text{ mVdc}$	$V_{BE(sat)}$		1.2	Vdc

**DYNAMIC CHARACTERISTICS**

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio $I_C = 500 \text{ mAdc}, V_{CE} = 15 \text{ Vdc}; f = 10 \text{ MHz}$	$ h_{fe} $	1.0	5.0	
Output Capacitance $V_{CB} = 15 \text{ Vdc}, I_E = 0, 100 \text{ kHz} \leq f \leq 1.0 \text{ MHz}$	$C_{obo}$		550	pF